/ Descriptions

PDFN3×3A-8L P MOS

P-Channel Enhancement Mode Field Effect Transistor in a PDFN3×3A-8L Plastic Package.

/ Features

V_{DS} (V) = -30V

I_D =-34 A (V_{GS} = ± 20V)

$R_{DS(ON)}$@10V ≤ 14mR(Typ.12.8mR)

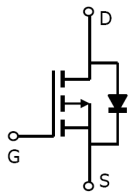
HF Product.

/ Applications

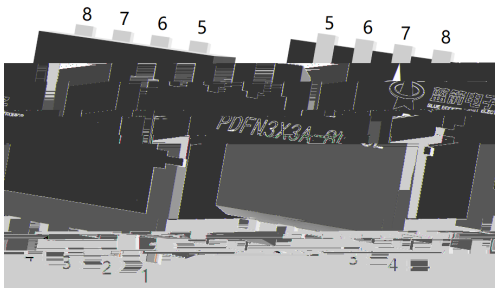
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



出脚	定义
Pin1	S
Pin2	S

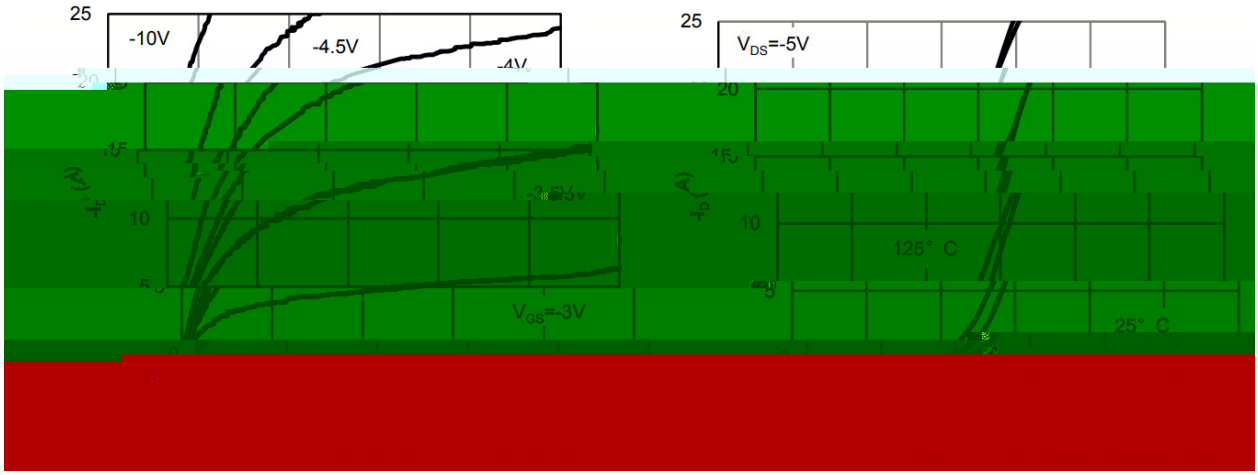
/ Marking

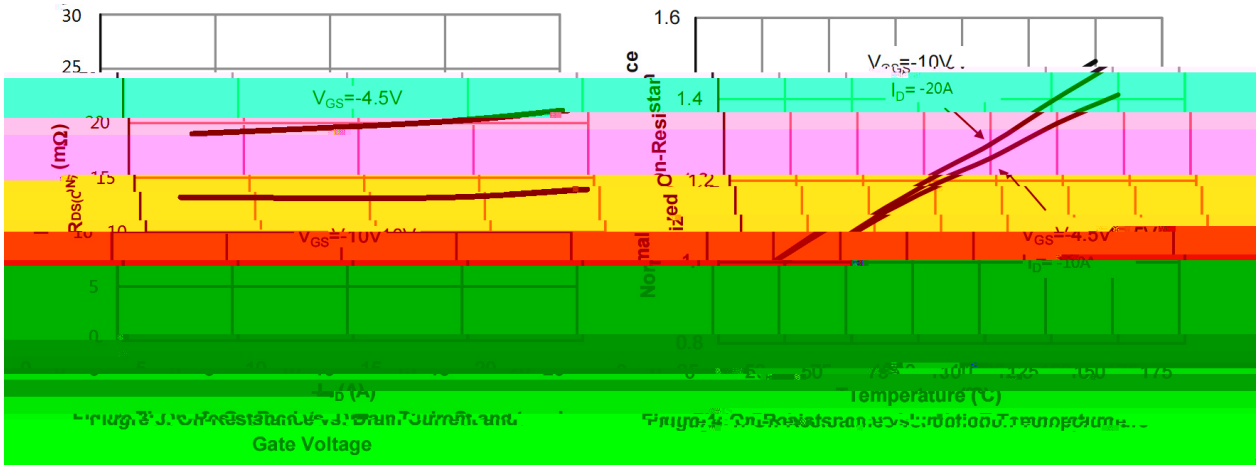
See Marking Instructions.

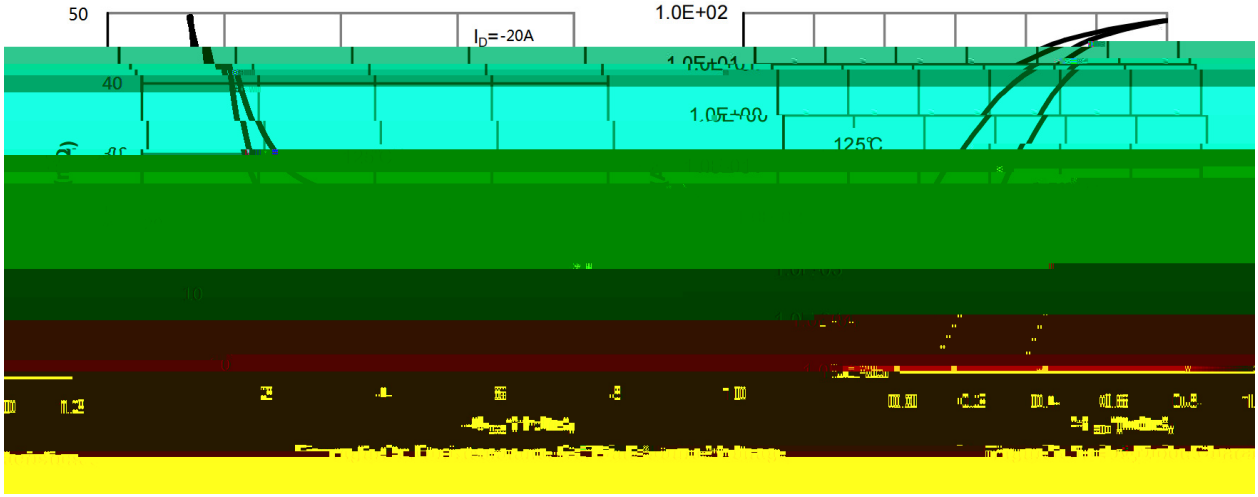
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-30	V
Drain Current	I_D(Tc=25)	-34	A

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=-250μA V_{GS}=0V	-30DSS		BV	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-30V				

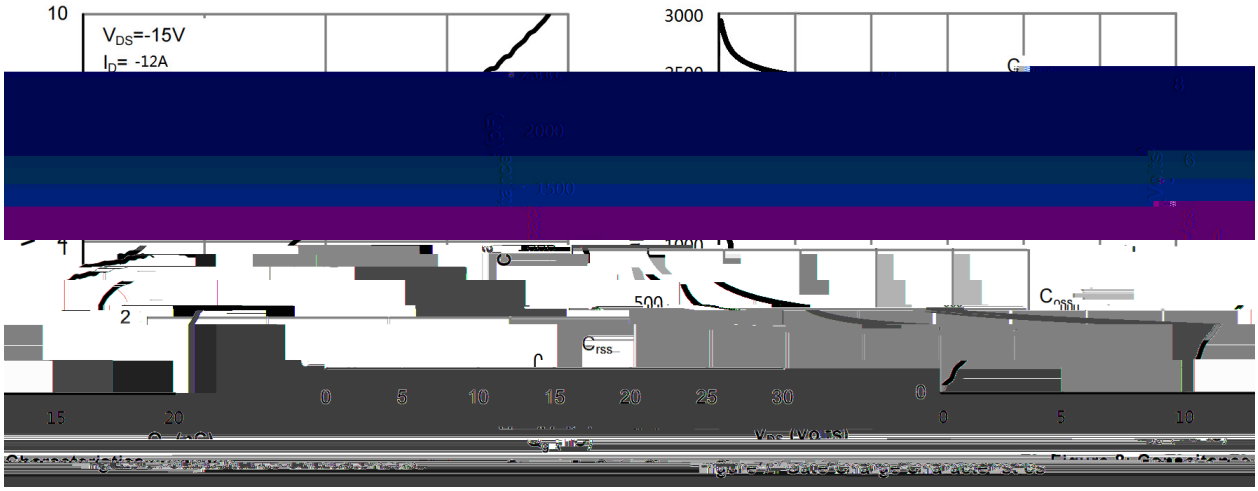
/ Electrical Characteristic Curve

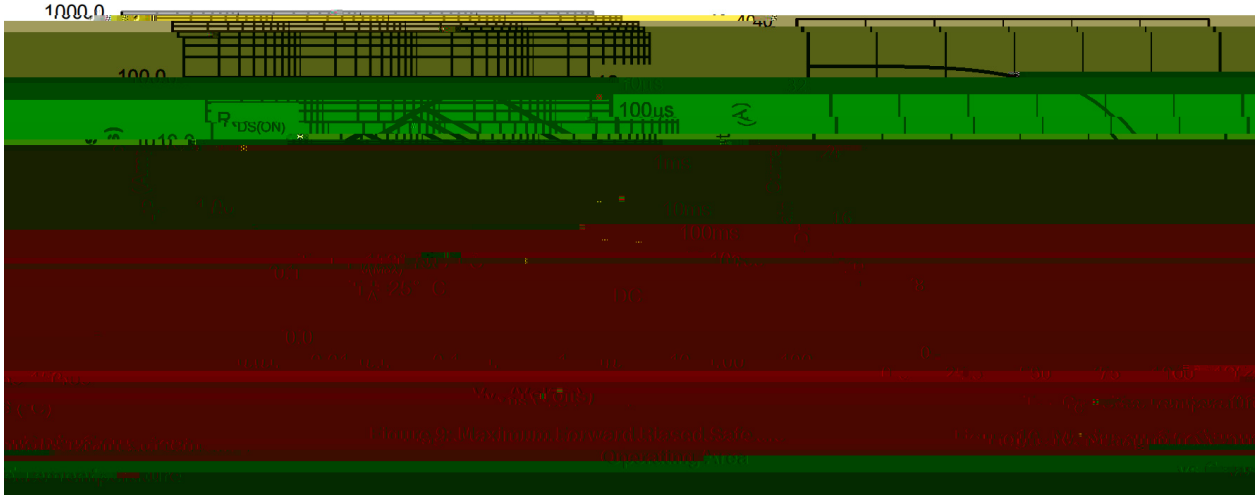


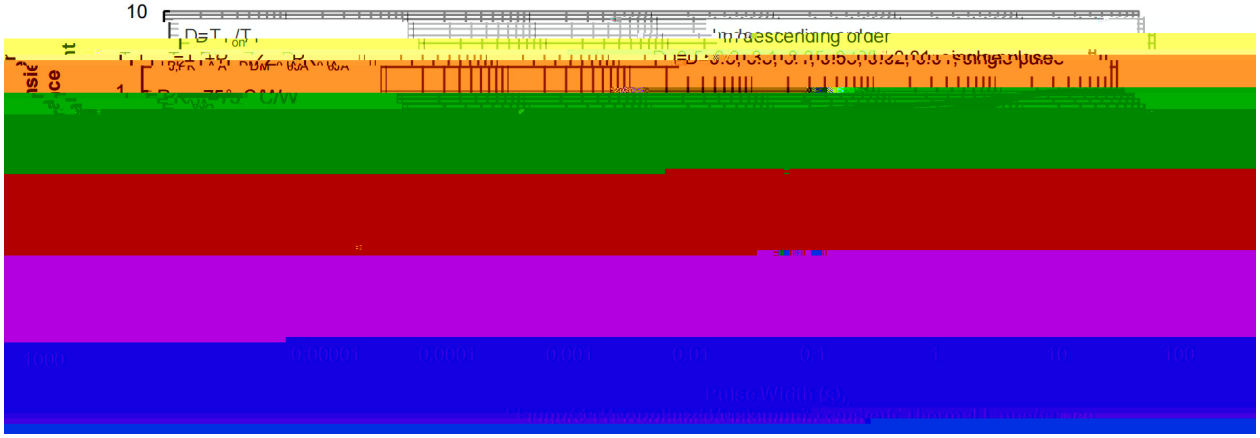




/ Electrical Characteristic Curve



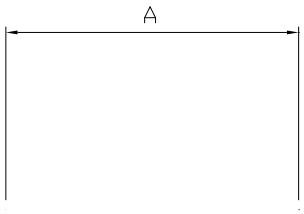




/ Package Dimensions

PDFN3X3A-8L

Unit:mm



Dimensions In Millimeterer			
Symbol	MIN	TYP	MAX
A	3.20	3.30	3.40
A1	3.10	3.15	3.20
B	3.20	3.30	3.40
B1	2.95	3.00	3.05

Rev.00 202011

/ Marking Instructions



BR

140P03

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Note:

BR:	Company Code
140P03:	Product Type Code
****:	Lot No. Code, code change with Lot No

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)
